

1     ABSTRACT OF THE DISCLOSURE

2             The invention includes a method of forming a semiconductor  
3 construction. A first substrate is provided which comprises silicon-  
4 containing structures separated from one another by an insulative  
5 material. The silicon-containing structures define an upper surface. A  
6 second semiconductor substrate is provided which comprises a  
7 monocrystalline material having a damage region therein. The second  
8 semiconductor substrate is bonded to the silicon-containing structures of  
9 the first substrate at the upper surface. The monocrystalline material  
10 is then cleaved along the damage region. The invention also  
11 encompasses a semiconductor construction comprising a first substrate  
12 having silicon-containing structures separated from one another by an  
13 insulative material, and a second substrate comprising a monocrystalline  
14 material. The silicon-containing structures of the first substrate define  
15 an upper surface, and the monocrystalline material of the second  
16 substrate is bonded over the silicon-containing structures at the upper  
17 surface.